

Jin Soak Kim

List of Publications by Year in descending order

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docs citations

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times ranked

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citing authors

#	ARTICLE	IF	CITATIONS
1	Nonpolar growth and characterization of a-plane InGaN/GaN quantum well structures with different indium compositions. <i>Solid-State Electronics</i> , 2010, 54, 1221-1226.	1.4	5
2	Zero-internal fields in nonpolar InGaN/GaN multi-quantum wells grown by the multi-buffer layer technique. <i>Nanotechnology</i> , 2010, 21, 134026.	2.6	12
3	Field dependence of barrier heights and luminescence properties in polar and nonpolar InGaN/GaN single quantum wells. <i>Applied Physics Letters</i> , 2009, 95, 182109.	3.3	3
4	Carrier Dynamics of Deep-Level States in InGaN/GaN Multiquantum Wells. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 06FF08.	1.5	3
5	Study on carrier trapping and emission processes in InAs/GaAs self-assembled quantum dots by varying filling pulse width during DLTS measurements. <i>Superlattices and Microstructures</i> , 2009, 46, 312-317.	3.1	9
6	Analysis of energy levels of InAs/GaAs self-assembled quantum dots by using C_V and V_C and deep level transient spectroscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2009, 246, 808-811.	1.5	0
7	Polarization effect on electronic band structure of InGaN/GaN multi-quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S731.	0.8	0
8	Carrier dynamics in energy states of InAs/GaAs quantum dots by measuring selective carrier filling and extracting techniques. , 2009, , .		0
9	Structural, electrical, and optical characterizations of a-plane InGaN/GaN quantum well structures. , 2009, , .		0
10	Dislocation related defect states in GaN irradiated with 1 MeV electron beam. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1630-1632.	0.8	0
11	Electrical and Optical Properties of p-Type InMnP:Zn for Nano-spintronics. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 5066-5069.	1.5	0
12	Relevant correlation between electrical and magnetic properties for p-type InP:Zn implanted with Mn (10 at.%). <i>Applied Physics Letters</i> , 2008, 93, .	3.3	1
13	Electrical and optical properties of p-type InMnP:Zn for nano-spintronics. , 2007, , .		0
14	Optical, structural, and magnetic properties of p-type GaN implanted with Fe ⁺ (5 and 10 at%). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007, 204, 78-85.	1.8	0
15	A study on the energy bands of multi-quantum wells in the quantum cascade laser structure by deep-level transient spectroscopy. <i>Semiconductor Science and Technology</i> , 2006, 21, 1069-1072.	2.0	1
16	Origin of clear ferromagnetism for p-type GaN implanted with Fe ⁺ (5 and 10at.%). <i>Applied Physics Letters</i> , 2006, 89, 082505.	3.3	17
17	Electrical properties of InAs/InGaAs/GaAs quantum-dot infrared photodetectors. , 2005, , .		0